

N-channel TrenchMOS standard level FET Rev. 03 — 31 May 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

Motors, lamps and solenoids

1.3 Applications

- 12 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data

Quick reference	uuu					
Parameter	Conditions		Min	Тур	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 3</u> ; see <u>Figure 1</u>	[1]	-	-	75	A
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
aracteristics						
drain-source on-state resistance	$\label{eq:GS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A}; \\ T_j = 175 \ ^\circ\text{C}; \\ \text{see } \underline{\text{Figure 11}}; \text{ see } \underline{\text{Figure 12}} \end{array}$		-	-	8.5	mΩ
	$\label{eq:GS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \ ^{\circ}\text{C}; \\ \text{see } \underline{\text{Figure 11}}; \text{ see } \underline{\text{Figure 12}} \end{array}$		-	3.9	4.5	mΩ
	Parameter drain-source voltage drain current total power dissipation aracteristics drain-source on-state	$\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline drain-source & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C \\ \hline voltage & & & & & \\ \hline drain current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; \\ see & Figure 3; see & Figure 1 \\ \hline total power & & & & \\ \hline total power & & & \\ \hline drain-source & & & \\ \hline drain-source & & & \\ \hline on-state & & & \\ \hline resistance & & & & \\ \hline v_{GS} = 10 \ V; \ I_D = 25 \ A; \\ \hline T_j = 175 \ ^\circ C; \\ see & Figure 11; see & Figure 12 \\ \hline v_{GS} = 10 \ V; \ I_D = 25 \ A; \\ \hline T_j = 25 \ ^\circ C; \\ \hline \end{tabular}$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions \\ \hline drain-source & T_j \ge 25 \ ^{\circ}C; \ T_j \le 175 \ ^{\circ}C & \\ \hline voltage & \\ \hline drain current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^{\circ}C; & \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min \\ \hline drain-source & $T_j \ge 25\ ^\circ C;\ T_j \le 175\ ^\circ C & -$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min & Typ \\ \hline drain-source & T_j \ge 25 \ ^\circ C; \ T_j \le 175 \ ^\circ C & - & - \\ \hline voltage & & & & & & & & & & & & & & \\ \hline drain current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^\circ C; & & & & & & & & & & & & \\ \hline total power & & & & & & & & & & & & & & & & & & \\ \hline total power & & & & & & & & & & & & & & & & & & &$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min & Typ & Max \\ \hline drain-source & T_j \ge 25 \ ^{\circ}C; \ T_j \le 175 \ ^{\circ}C & - & - & 40 \\ \hline drain current & V_{GS} = 10 \ V; \ T_{mb} = 25 \ ^{\circ}C; & 11 & - & - & 75 \\ \hline see & Figure 3; \ see & Figure 1 & - & - & 75 \\ \hline total power & T_{mb} = 25 \ ^{\circ}C; \ see & Figure 2 & - & - & 300 \\ \hline total power & T_{mb} = 25 \ ^{\circ}C; \ see & Figure 2 & - & - & 300 \\ \hline aracteristics & & & & & & & & \\ \hline drain-source & V_{GS} = 10 \ V; \ I_D = 25 \ A; & & & & & & & & & \\ \hline resistance & & & & & & & & & & & & & \\ \hline v_{GS} = 10 \ V; \ I_D = 25 \ A; & & & & & & & & & & & & & & & & & & $

Avalanche ruggedness

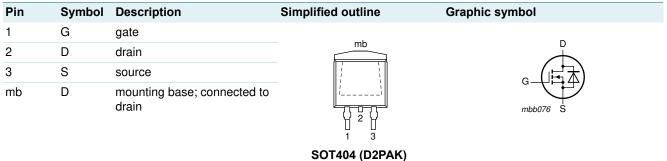


Table 1.	Quick reference datacontinued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; V_{sup} \leq 40 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 10 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	1.6	J
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 32 \text{ V}; T_j = 25 \text{ °C};$ see Figure 13	-	50	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2.Pinning information



3. Ordering information

Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
BUK7604-40A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

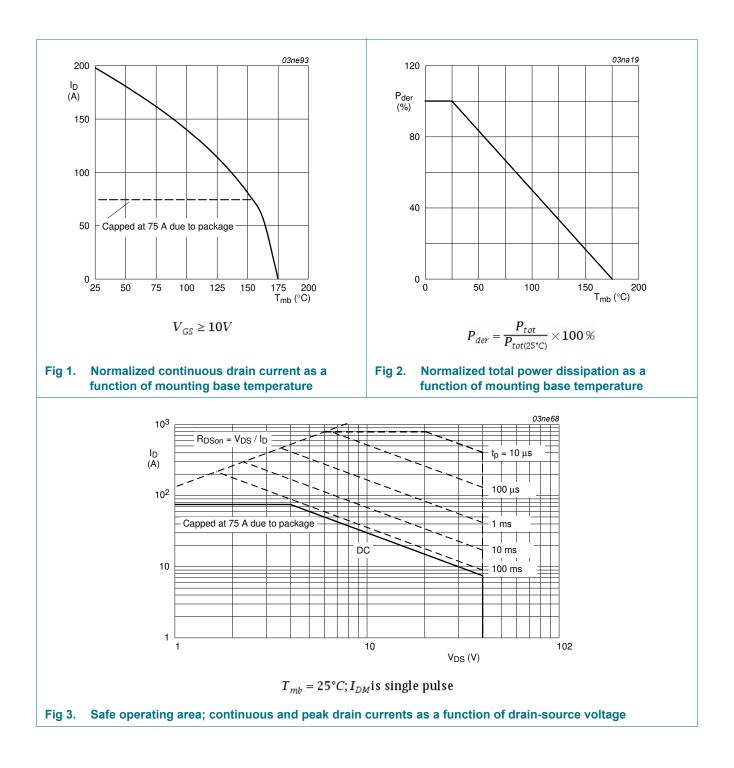
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	40	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 3</u> ; see <u>Figure 1</u>	<u>[1]</u>	-	-	198	A
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[2]	-	-	75	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 3</u> ; see <u>Figure 1</u>	[2]	-	-	75	A
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u>		-	-	794	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-draii	n diode						
ls	source current	T _{mb} = 25 °C	<u>[1]</u>	-	-	198	А
			[2]	-	-	75	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	794	А
Avalanche r	uggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 40 \ V; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \ V; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped \end{array}$		-	-	1.6	J

[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.

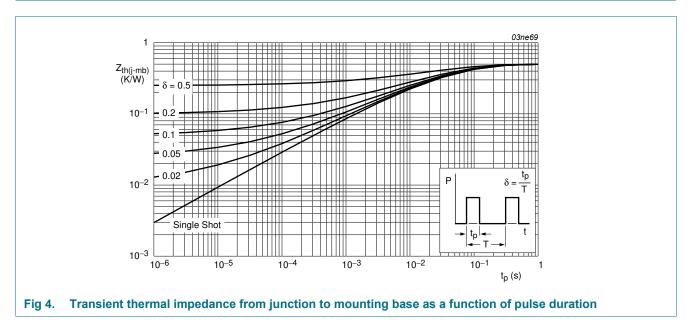
BUK7604-40A

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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W



Characteristics 6.

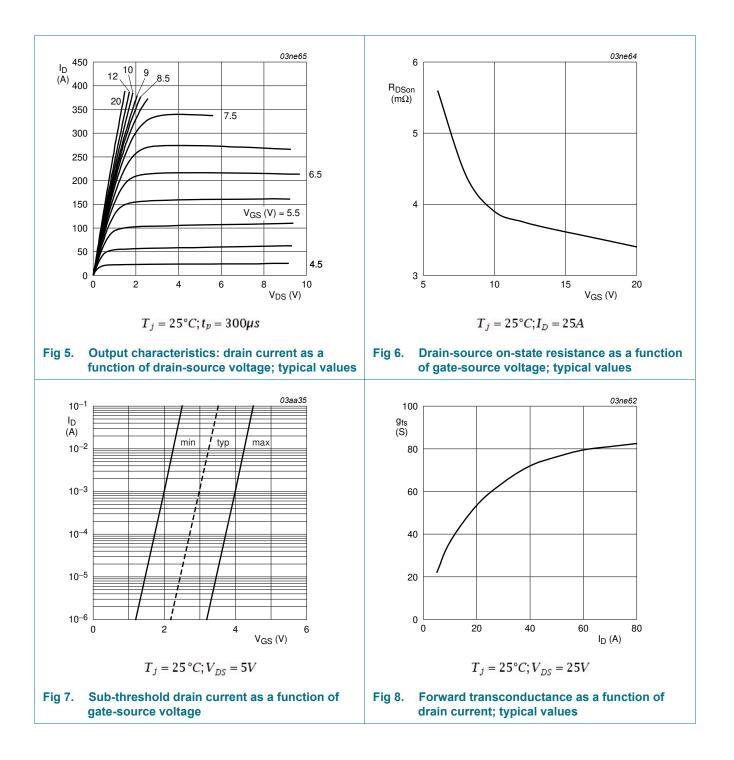
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{V}; T_j = -55 ^\circ\text{C}$	36	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	40	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 20 V; T _j = 25 °C	-	2	100	nA
		V _{DS} = 0 V; V _{GS} = -20 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	8.5	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 11; see Figure 12	-	3.9	4.5	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	117	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 13</u>	-	19	-	nC
Q _{GD}	gate-drain charge		-	50	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	4300	5730	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 14$	-	1400	1680	pF
C _{rss}	reverse transfer capacitance		-	800	1100	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_{L} = 1.2 Ω ; V_{GS} = 10 V;	-	33	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	110	-	ns
t _{d(off)}	turn-off delay time		-	151	-	ns
t _f	fall time		-	76	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_i = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S} = 20 \text{ A}; \text{ dI}_{\rm S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	96	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _i = 25 °C		224	-	nC

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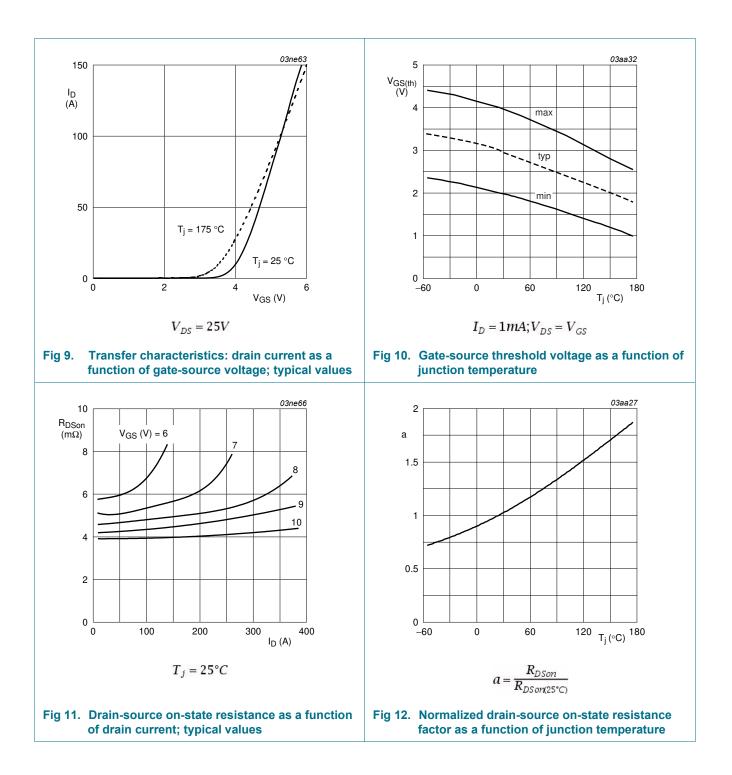
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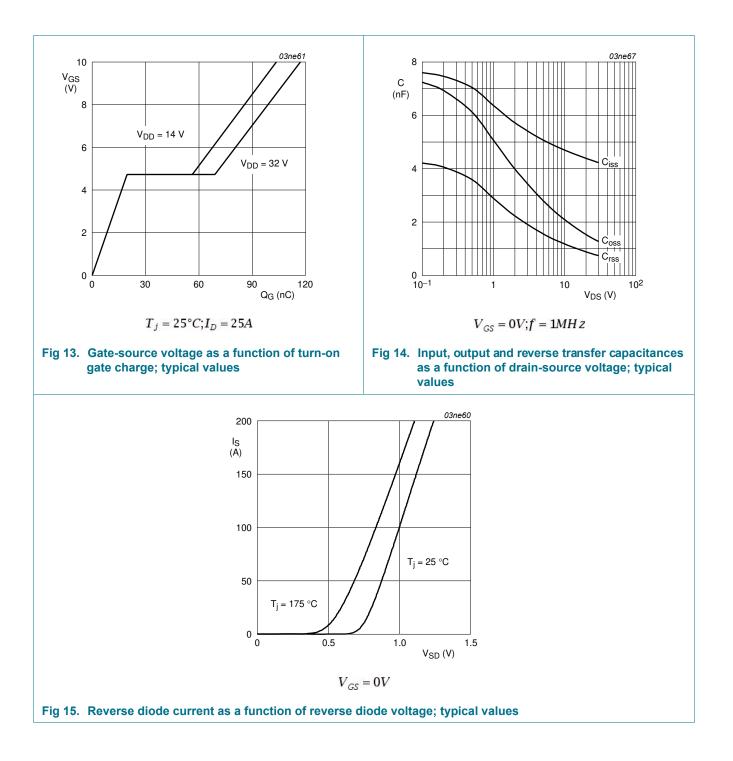
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7. Package outline

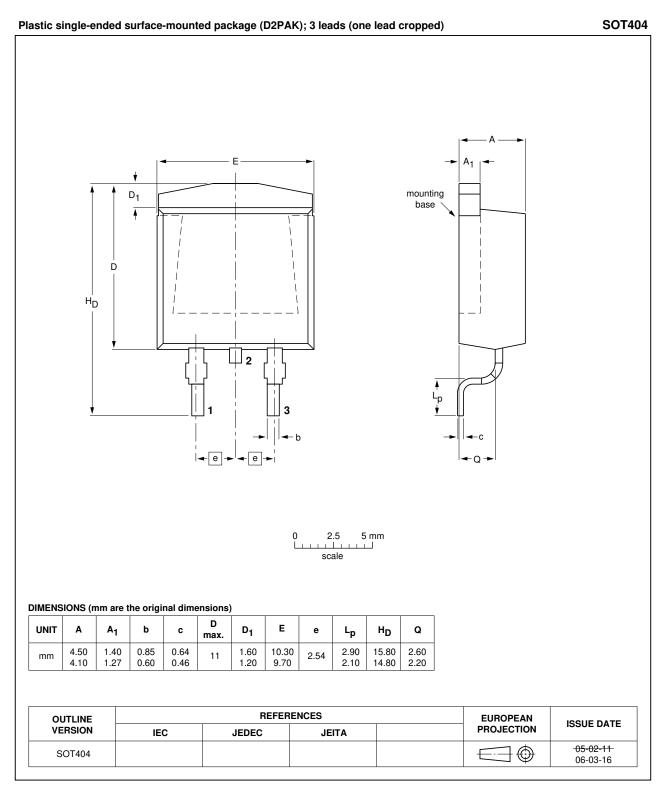


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7.	Revision history				
Documen	t ID	Release date	Data sheet status	Change notice	Supersedes
BUK7604-	40A v.3	20100531	Product data sheet	-	BUK75045_7604_7E04_40A_2
Modificatio	ons:		of this data sheet has of NXP Semiconductor	•	to comply with the new identity
		 Legal texts 	have been adapted to	the new company	name where appropriate.
		• •	er BUK7604-40A sepa 7604_7E04_40A_2	rated from data sh	neet
BUK7504	5_7604_7E04_40A_2	20011107	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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